

ESD73011N

**1-Line, Bi-directional, Ultra-low Capacitance
Transient Voltage Suppressors**

<http://www.willsemi.com>

Descriptions

The ESD73011N is an ultra-low capacitance TVS (Transient Voltage Suppressor) designed to protect high speed data interfaces. It has been specifically designed to protect sensitive electronic components which are connected to data and transmission lines from over-stress caused by ESD (Electrostatic Discharge).

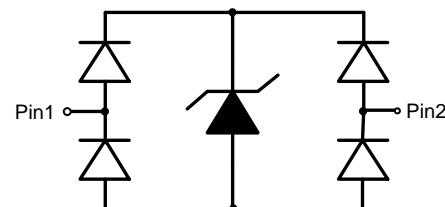
The ESD73011N incorporates one pair of ultra-low capacitance steering diodes plus a TVS diode.

The ESD73011N may be used to provide ESD protection up to $\pm 20\text{kV}$ (contact discharge) according to IEC61000-4-2, and withstand peak pulse current up to 5.5A ($8/20\mu\text{s}$) according to IEC61000-4-5.

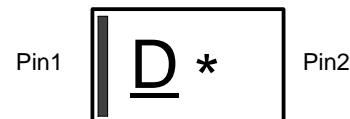
The ESD73011N is available in DFN1006-2L package. Standard products are Pb-free and Halogen-free.



DFN1006-2L (Bottom View)



Pin configuration



D = Device code

* = Month code (A~Z)

Marking (Top View)

Order information

Device	Package	Shipping
ESD73011N-2/TR	DFN1006-2L	10000/Tape&Reel

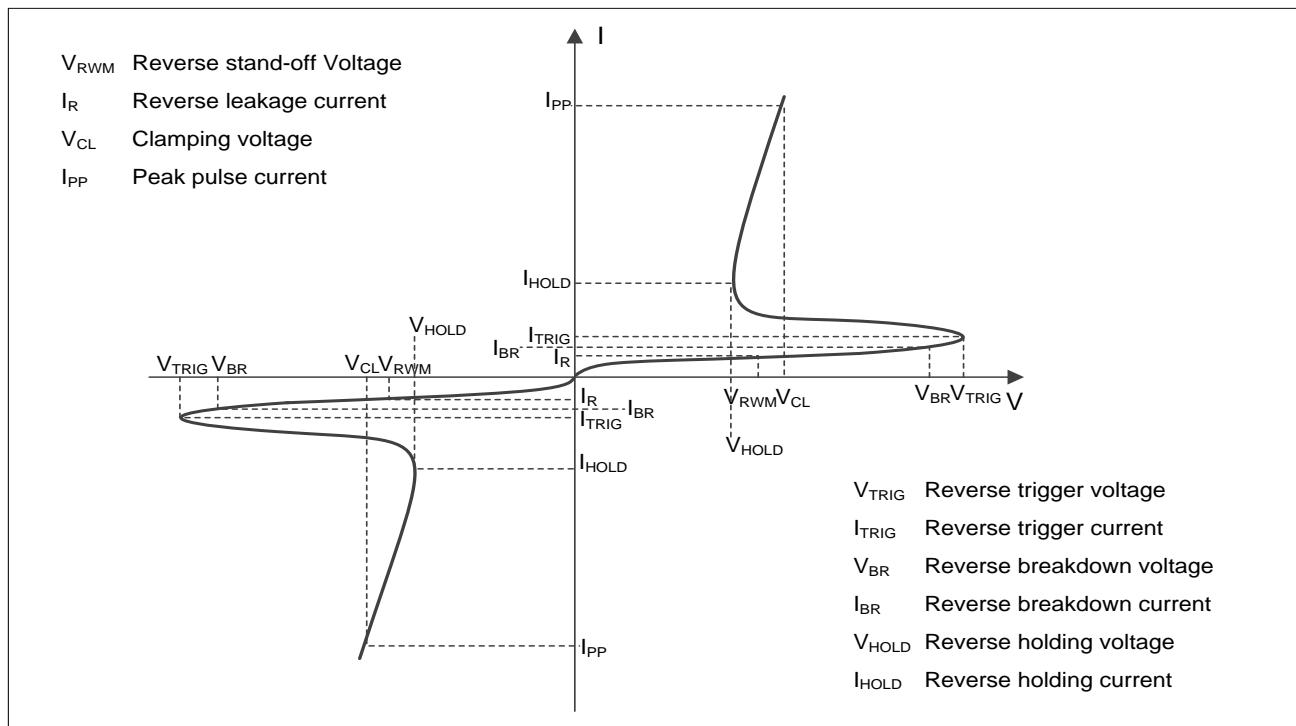
Applications

- USB 2.0 and USB 3.0
- HDMI 1.3 and HDMI 1.4
- SATA and eSATA
- DVI
- IEEE 1394
- PCI Express
- Portable Electronics
- Notebooks

Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu s$)	P_{pk}	46	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	5.5	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 20	kV
ESD according to IEC61000-4-2 contact discharge		± 20	
Operation junction temperature	T_J	125	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

Electrical characteristics ($T_A=25^{\circ}C$, unless otherwise noted)



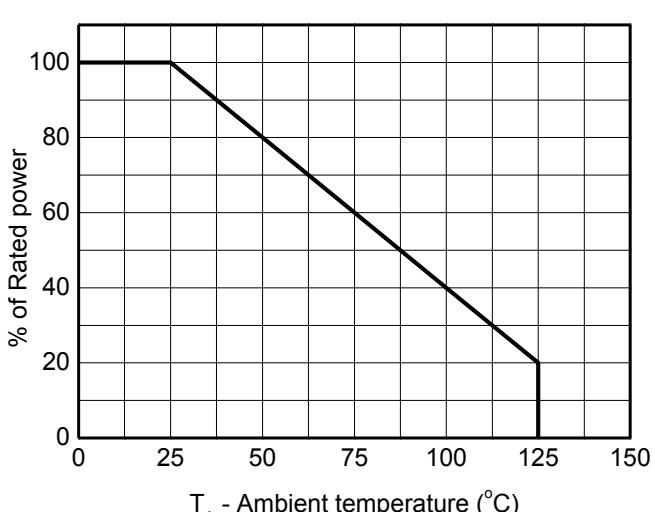
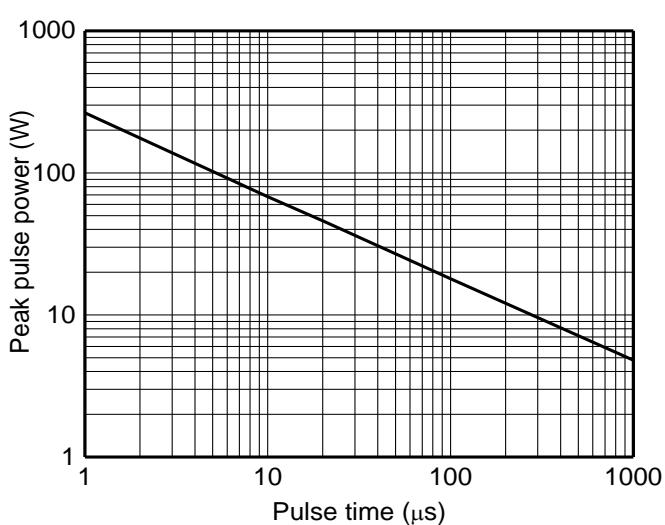
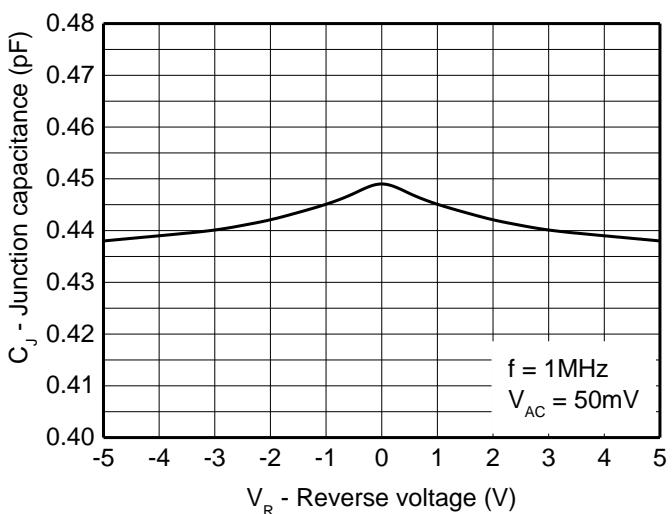
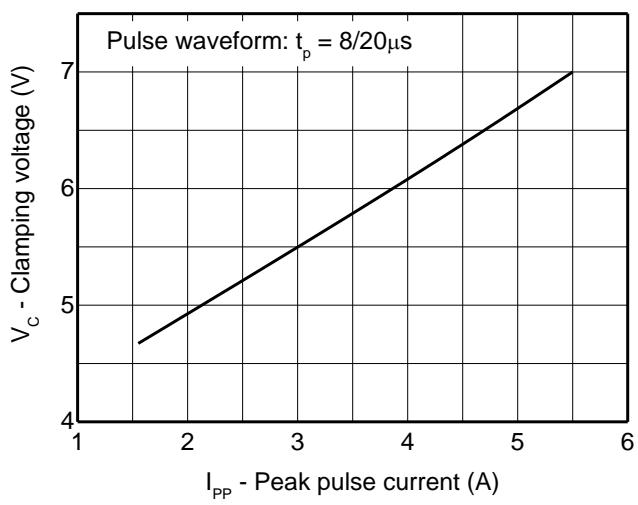
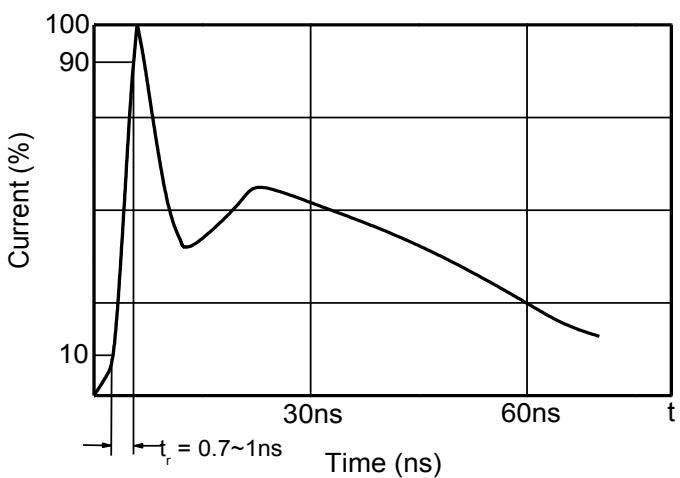
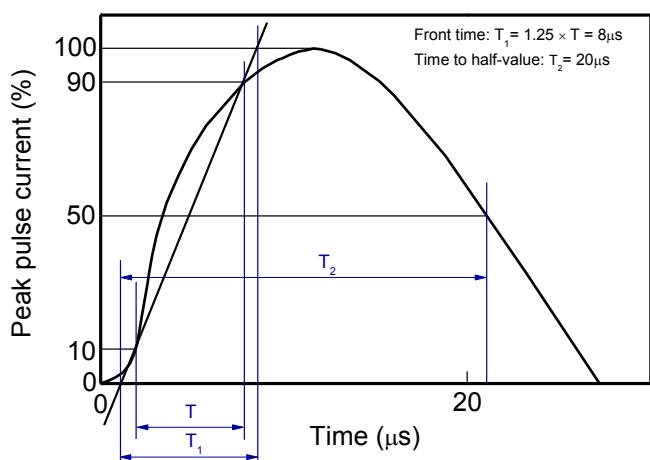
Definitions of electrical characteristics

Electrical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

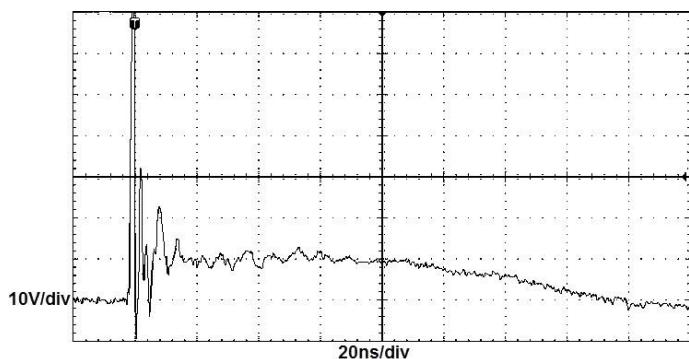
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse maximum working voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	$V_{RWM} = 5\text{V}$		<1	50	nA
Reverse breakdown voltage	V_{BR}	$I_T = 1\text{mA}$	7.0			V
Clamping voltage ¹⁾	V_{CL}	$I_{PP} = 16\text{A}, t_p = 100\text{ns}$		9.5		V
Dynamic resistance ¹⁾	R_{DYN}			0.30		Ω
Clamping voltage ²⁾	V_{CL}	$V_{ESD} = 8\text{kV}$		9.5		V
Clamping voltage ³⁾	V_{CL}	$I_{PP} = 1\text{A}, t_p = 8/20\mu\text{s}$			5.5	V
		$I_{PP} = 5.5\text{A}, t_p = 8/20\mu\text{s}$			8.5	V
Junction capacitance	C_J	$V_R = 0\text{V}, f = 1\text{MHz}$ Any I/O pin to GND		0.45	0.65	pF

Notes:

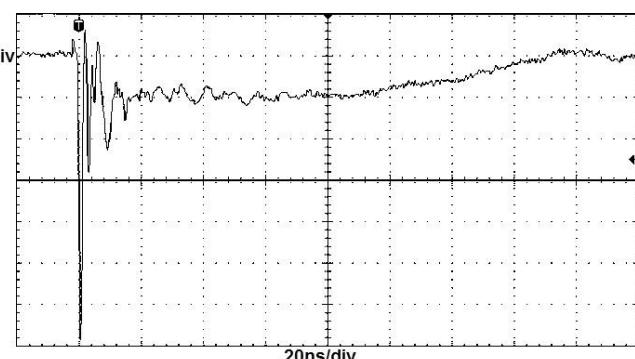
- 1) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100\text{ns}$, $t_r = 2\text{ns}$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)


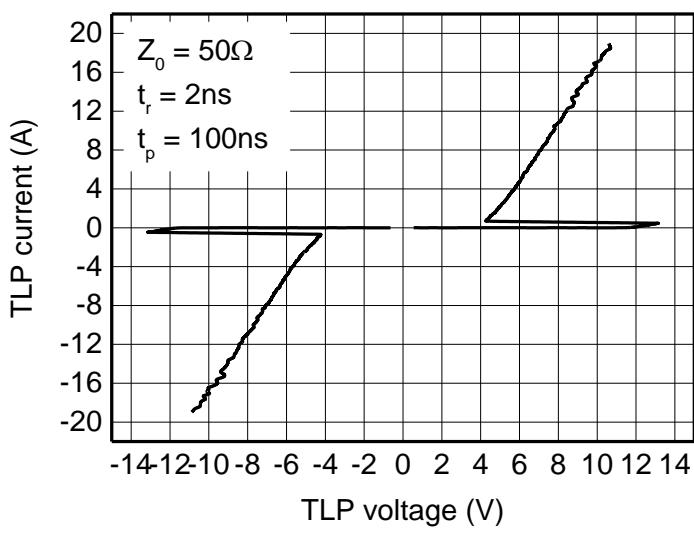
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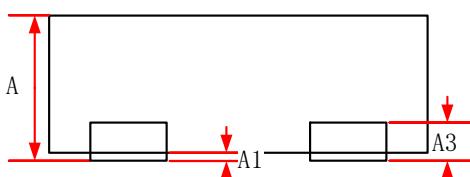
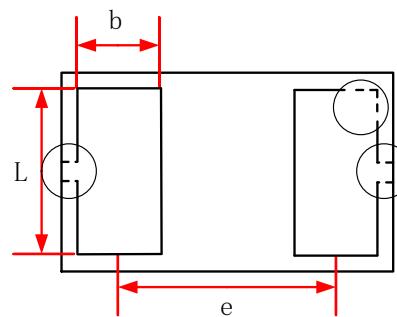
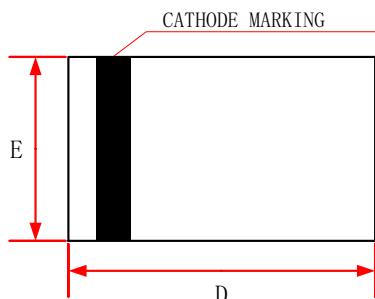


ESD clamping
(+8kV contact discharge per IEC61000-4-2)

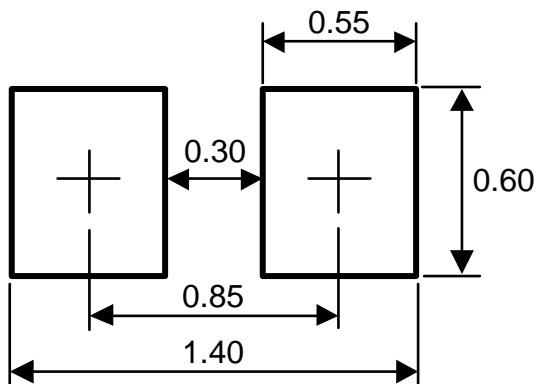


ESD clamping
(-8kV contact discharge per IEC61000-4-2)



Package outline dimensions
DFN1006-2L


	Min.	Typ.	Max.
A	0.30	-	0.50
A1	0.00	-	0.05
A3	0.125 Ref.		
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.20	0.25	0.30
L	0.45	0.50	0.55
e	0.65 Typ.		

Recommend land pattern (Unit: mm)

Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.